

IVPS100A - Improved Vertical Parallel Structure

Tip width characterizer with an array of 5 lines 100 nm wide and a single line 100 nm wide for larger tips.

planes).

Sidewalls are vertical and parallel (111-crystal

Specifications

Material Silicon

100 nm

Width of line actual linewidth is delivered for each

chip

Pitch 500 nm ± 10nm

Depth of line ~ 1 µm

Surface/sidewall angle < 90° ± 0,5°

Sidewall parallelity < 1°

Top corner radius < 10 nm

Also well suited as SEM standard

Probe tip characterizers are used to check the shape and the dimension of the probe tip.

Each cell is numbered, which facilitates recalibration at the identical position.

Layout:

81 cells on 1 x 1 mm area, on 6 x 6 mm silicon chip